

Claim 7, line 7, delete "of" (second occurrence) insert
--at--.

Claim 11, line 8, delete "of" (first occurrence) insert
--at--;

line 13, before "a" insert --setting--;

line 14, delete "is set"; same line 14, delete "and"
insert --, whereby--.

Claim 14, line 3, delete "?m" insert -- μ m--.

15. (amended) A method according to claim 14, wherein
A' the electrostatic [B] chucking of the sample is [that of]
effected by a dipole type electrostatic chuck.

18. (amended) A sample surface treating apparatus
comprising:

A2 a stage which is provided in a chamber and on which a
sample to be subjected to a surface treatment is to be placed;
etching gas supplying means for continuously supplying an
etching gas for plasma generation into the chamber;
plasma generating means for generating a high-density
plasma in the chamber;
a bias power supply for applying a bias voltage of 100
kHz or higher to the stage independently of the plasma
generation; and
pulse modulating means for modulating the bias power